FIG. 9

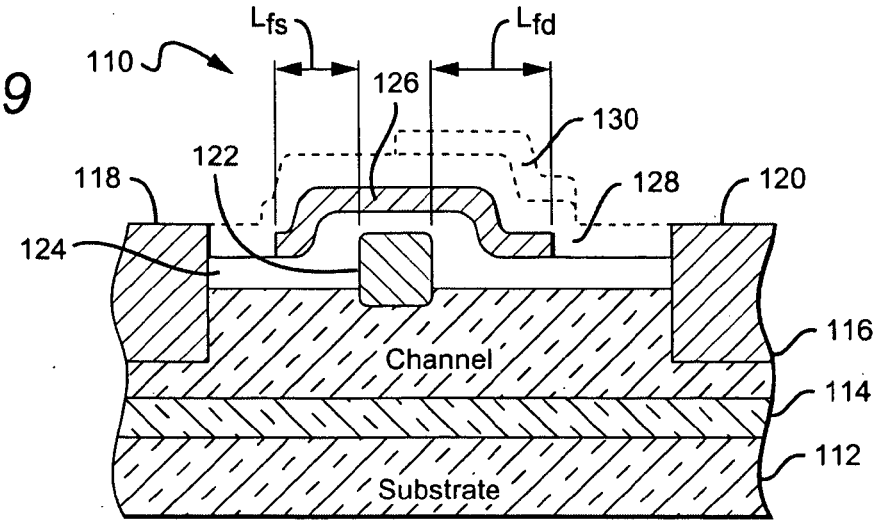

FIG. 10

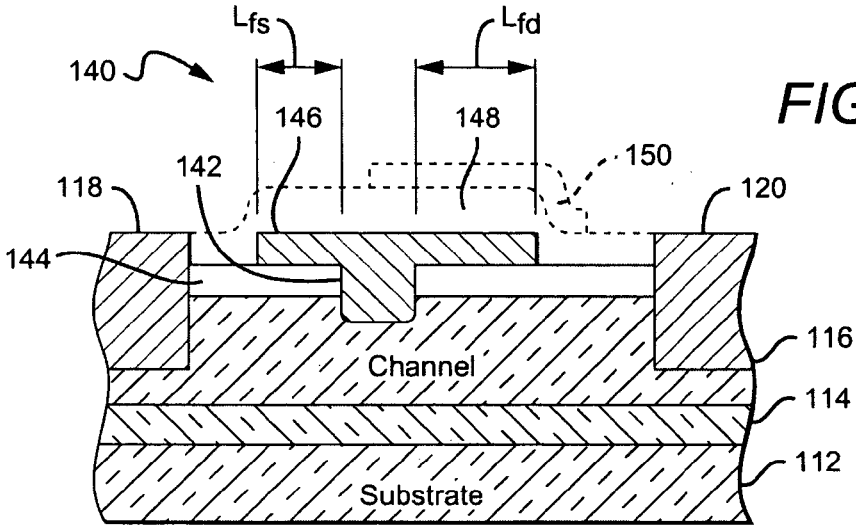

FIG. 11

130

	I_d, max: before/after (mA/mm)	Pinch-off V_t: before/after (V)	I_g at -25V: before/after (mA/mm)	Output power: before/after (dBm)
Device A: no gate-source FP	1061 / Broke down	-3.62 / Broke down	0.148 / Broke down	30.36 / Broke down
Device B: with gate- source FP of 0.2 μm long	1056 / 1043	-3.55 / -3.41	0.114 / 0.370	30.50 / 30.40